

SPECIFICATION OF LED CHIP

C630-35V

[Red]

1) Commodity Type and Physical Characteristics.

1. Material	InGaAlP/GaAs	
2. Electrode	Top Side P (anode)side	:Au Alloy/ Pad
	Bottom Side N (cathode)side	:Au Alloy
3. Electrode Pattern		Fig.1
4. Chip Size		Fig.2
5. Chip Thickness		Fig.2
6. Emission Area		Fig.2

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=20mA		1.9	2.4	V
Reverse Current	Ir	Vr=5V			10	uA
Brightness	Iv	If=20mA	40	90		mcd
Power Intensity	Po	If=20mA	0.7	1.2		mW
Peak Wavelength	λ_P	If=20mA	620	630	640	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		20		nm
RiseTime	tr	If=20mA		100		ns
FallTime	tf	If=20mA		100		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

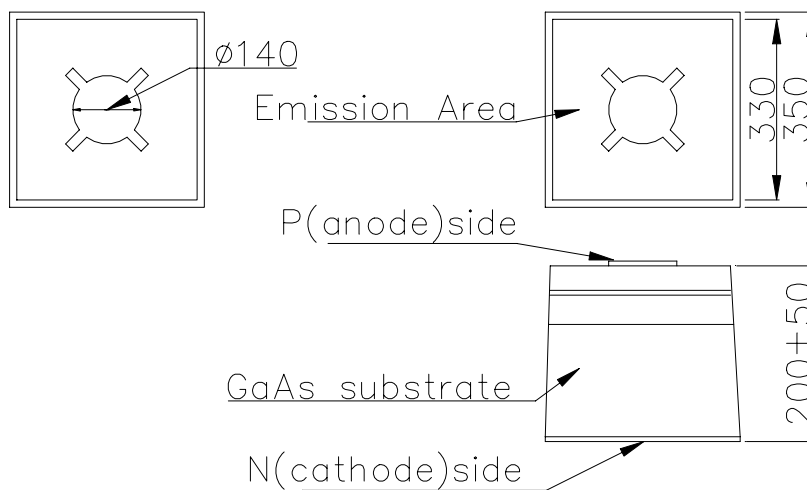


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area